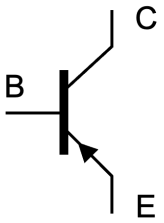
GOOD-ARK
SEMICONDUCTOR

MJE350
PNP Power Transistor

Features

- Collector-emitter sustaining voltage $V_{CEO(SUS)}$=-270V (Min)
- DC current gain h_{FE}=-100 (Min) @ I_C=-50mA
- Low collector saturation voltage $V_{CE(sat)}$=-1.0V (Max.) @ I_C=-50mA
- Complement to the NPN MJE340
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

TO-126



Schematic Diagram

APPLICATIONS

- Designed for high voltage and general purpose applications.

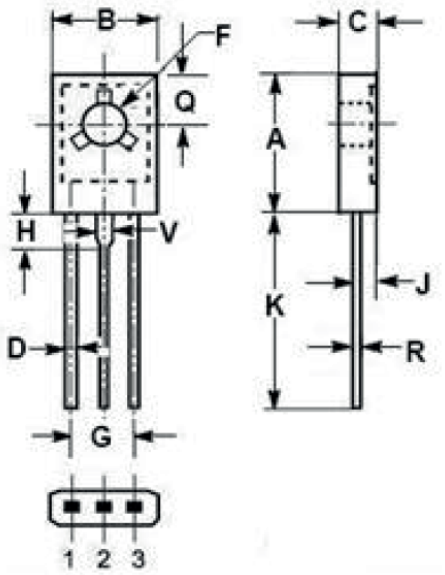
Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-260	V
Emitter-Base Voltage	V_{EBO}	-3	V
Collector Current-Continuous	I_C	-0.5	A
Collector Power Dissipation T_C=25℃	P_C	20	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-65 to +150	°C
Thermal Resistance, Junction to Case (Max)	$R_{thj\text{-}c}$	6.25	°C/W

Electrical Characteristics (T_C=25°C unless otherwise specified)

PARAMETER	Symbol	Conditions	Min	Max	Unit
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	I_C=-1.0mA, I_B=0	-260	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-1.0mA, I_E=0	-300	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=--1.0mA, I_C=0	-3	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-50mA, I_B=-5mA	-	-1.0	V
Collector Cutoff Current	I_{CBO}	V_{CB}=-300V, I_E=0	-	-0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB}=-3V, I_C=0	-	-0.1	mA
DC Current Gain	h_{FE}	I_C=-50mA, V_{CE}=-10V	30	240	-

Package Outline Dimensions (TO-126)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	10.70	10.95	0.421	0.431
B	7.70	7.90	0.303	0.311
C	2.60	2.80	0.102	0.110
D	0.66	0.86	0.026	0.034
F	3.10	3.30	0.122	0.130
G	4.48	4.68	0.176	0.184
H	2.00	2.20	0.079	0.087
J	1.35	1.55	0.053	0.061
K	15.30	16.30	0.602	0.642
Q	3.70	3.90	0.146	0.154
R	0.40	0.60	0.016	0.024
V	1.17	1.37	0.046	0.054